

1. Record Nr.	UNINA9910300410703321
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Titolo	High-Resolution Spin-Resolved Photoemission Spectrometer and the Rashba Effect in Bismuth Thin Films // by Akari Takayama
Pubbl/distr/stampa	Tokyo : , : Springer Japan : , : Imprint : Springer, , 2015
ISBN	4-431-55028-3
Edizione	[1st ed. 2015.]
Descrizione fisica	1 online resource (92 p.)
Collana	Springer Theses, Recognizing Outstanding Ph.D. Research, , 2190-5053
Disciplina	530 530.417 530.8 537.622
Soggetti	Surfaces (Physics) Interfaces (Physical sciences) Thin films Spectrum analysis Microscopy Materials—Surfaces Physical measurements Measurement Semiconductors Surface and Interface Science, Thin Films Spectroscopy and Microscopy Surfaces and Interfaces, Thin Films Measurement Science and Instrumentation
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	Description based upon print version of record.
Nota di bibliografia	Includes bibliographical references.
Nota di contenuto	Introduction -- Basic Principle of Photoemission Spectroscopy and Spin Detector -- Development of High Resolution Spin-Resolved Photoemission Spectrometer -- Anomalous Rashba Effect of a Bi Thin Film on Si(111) -- Rashba Effect at Interface of a Bi Thin Film on Si(111) -- Conclusion.

Sommario/riassunto

In this thesis, the author has developed a high-resolution spin-resolved photoemission spectrometer that achieves the world-best energy resolution of 8 meV. The author has designed a new, highly efficient mini Mott detector that has a large electron acceptance angle and an atomically flat gold target to enhance the efficiency of detecting scattered electrons. The author measured the electron and spin structure of Bi thin film grown on a Si(111) surface to study the Rashba effect. Unlike the conventional Rashba splitting, an asymmetric in-plane spin polarization and a tremendous out-of-plane spin component were observed. Moreover, the author found that the spin polarization of Rashba surface states is reduced by decreasing the film thickness, which indicates the considerable interaction of Rashba spin-split states between the surface and Bi/Si interface.
